VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claim 1 has been amended as follows:

--1. (amended) A semiconductor device comprising:

an interconnection board having first and second surfaces; and

a high rigidity plate securely fixed to and directly in contact with at least a majority of said second surface of said interconnection board,

said high rigidity plate being higher in rigidity than said interconnection board for suppressing said interconnection board from being bent upon receipt of any stress applied during at least a process for manufacturing said interconnection board.

Claim 8 has been amended as follows:

--8. (amended) A semiconductor device comprising:

an interconnection board having first and second surfaces;

at least [a] one semiconductor chip mounted on said first surface of said interconnection board; and

a high rigidity plate securely fixed to and directly in contact with at least a majority of said second surface of said interconnection board,

said high rigidity plate being higher in rigidity than said interconnection board for suppressing said interconnection board from being bent upon receipt of any stress applied during at least processes for manufacturing said interconnection board and for mounting said at least one semiconductor chip on said

first surface.--

Claim 18 has been amended as follows:

--18. (amended) A semiconductor device comprising:

an interconnection board having first and second surfaces;

at least one external electrode pad buried in said interconnection board,

said at least one external electrode pad having an exposed surface level with said second surface so that said second surface and said exposed surface form a single flat plane;

at least a semiconductor chip mounted on said first surface of said interconnection board; and

a buffer layer having a first surface in contact with said second surface of said interconnection board and also said buffer layer having a second surface on which at least [an] one external electrode is provided, and said buffer layer [having] providing at least [an] one electrical contact between said [interconnection board] one external electrode pad and said at least one external electrode, and said buffer layer being capable of absorbing and/or relaxing a stress applied to said at least external electrode to make said interconnection board free from application of said stress.--

Claim 37 has been amended as follows:

--37. (amended) The semiconductor device as claimed in claim [35] 36, wherein said supporting layer further comprises:

a supporting plate having plural holes[,] into which holes said external electrodes are inserted, and said supporting

plate extending in parallel to said second surface of said buffer layer to form an inter-space between said supporting plate and said second surface of said buffer layer; and

a supporting sealing resin material filling said inter-space and surrounding parts of said external electrodes so that said supporting sealing resin material is in [tightly] tight contact with said parts of said external electrodes for supporting said external electrodes.--

Claim 38 has been amended as follows:

--38. (amended) The semiconductor device as claimed in claim 18, wherein said at least semiconductor chip is bonded via bumps to said [second] first surface of said interconnection board.--

Claim 43 has been amended as follows:

--43. (amended) A semiconductor device comprising:

an interconnection board having first and second surfaces;

at least one external electrode pad buried in said interconnection board,

said at least one external electrode pad having an exposed surface level with said second surface so that said second surface and said exposed surface form a single flat plane;

at least a semiconductor chip mounted on said first surface of said interconnection board;

at least one external electrode[s] fixed to said at least one external electrode pad[s] [on said second surface of said interconnection board]; and

a supporting layer on said second surface of said interconnection board for supporting said external electrodes.--

Claim 44 has been amended as follows:

--44. (amended) The semiconductor device as claimed in claim 43, further comprising:

a buffer layer having a first surface in contact with said second surface of said interconnection board, and

wherein said supporting layer further comprises[:]

a supporting plate having plural holes[,] into which holes said external electrodes are inserted, and said supporting plate extending in parallel to said second surface of said buffer layer to form an inter-space between said supporting plate and said second surface of said buffer layer; and

a supporting sealing resin material filling said inter-space and surrounding parts of said external electrodes so that said supporting sealing resin material is in [tightly] tight contact with said parts of said external electrodes for supporting said external electrodes.--

Claim 45 has been amended as follows:

--45. (amended) The semiconductor device as claimed in claim 43, wherein said at least semiconductor chip is bonded via bumps to said [second] first surface of said interconnection board.--

Claim 49 has been amended as follows:

--49. (amended) The semiconductor device as claimed in claim 48, further comprising:

a buffer layer having a first surface in contact with

said second surface of said interconnection board;

a stiffener extending on a peripheral region of said buffer layer; and

at least a heat spreader provided on said at least semiconductor chip and on said stiffener.--